

CLAIM AMENDMENTS

Please amend claims 10 and 14, without prejudice, as indicated on the following listing of all the claims in the present application after this Amendment:

1 – 9. (Cancelled)

10. (Currently Amended) In a flash memory system having an array of non-volatile memory cells arranged in blocks as a unit of erase, pages therein as a unit of data programming and reading, and planes of a plurality of blocks that are independently accessible, a method of operation of the memory system, comprising:

logically forming metablocks that individually include ~~[[a]]~~ blocks from a plurality of the planes,

sequentially receiving write commands with a varying number of units of data and logical addresses of the individual units of data, ~~and~~

determining from the write commands whether (1) a given one or more units of data having consecutive logical addresses are being received or (2) more than said given number of one or more units of data having consecutive logical addresses are being received, and

writing all the data received with individual write commands by (1), in response to determining that the given one or more units of data having consecutive logical addresses are being received, [[by]] writing [[a]] the given one or more units of data having consecutive logical addresses-sequentially into at least one page pages within at least one of the individual blocks of only one of the planes, and (2), in response to determining that more than said given number of one or more units of data having consecutive logical addresses are being received, [[by]] writing the more than said given number of units of data having consecutive logical addresses in parallel into pages within two or more blocks of one of the metablocks in two or more planes.

11. (Previously presented) The method of claim 10, additionally comprising writing an indication into non-volatile memory cells at the same time as the received data that identifies the blocks into which the data are being written in parallel.

12 – 13. (Cancelled)

14. (Currently Amended) In a flash memory system having an array a plurality of non-volatile memory cells arranged in a plurality of blocks of memory cells as a unit of erase that are provided in a plurality of sub-arrays and multiple pages within individual blocks as units of data programming and reading, a method of operation of the memory system, comprising:

logically forming metablocks that individually include blocks from a plurality of the sub-arrays,

sequentially receiving individual write commands with a number of sectors of data to be written into either a single page or into a plurality of pages,

in response to receiving the write commands with a number of sectors of data for a plurality of pages, writing all the received data in parallel into pages within a plurality of blocks of at least one of the metablocks in a plurality of the sub-arrays,

in response to receiving the write commands with a number of one or more sectors of data for only a single page of data, writing all the received data in parallel into individual pages of individual blocks of only one of the sub-arrays, and

maintaining indications in the non-volatile memory cells that are associated with the written sectors of data as to whether the individual sectors have been written in logical sequence with other sectors of data received with the same write command as the individual sector in either (1) a single block or (2) a plurality of blocks of a metablock.

15. (Previously presented) The method of claim 14, wherein a file allocation table (FAT) is stored within the non-volatile memory cells and the sectors of data for a single page of data include data of the FAT .

16. (Previously presented) The method of claim 14, additionally comprising storing the indications with their respective sectors of data as part of headers thereto.